

1090 MP

90 Watts, 50 Volts, Pulsed Avionics 1025 - 1150 MHz

GENERAL DESCRIPTION The 1090MP is a COMMON BASE bipolar the pulsed systems in the frequency band 1025-11 includes input prematch for broadband capability film metallization for proven highest MTTF. reduces junction temperature, extends life.	ansistor. It is designed for 50 MHz. The transistor lity. The device has gold thin- Low thermal resistance package	CASE OUTLINE 55FU, STYLE 1
Maximum Power Dissipation @ 25°C ²	250 Watts Peak	
Maximum Voltage and Current		
BVces Collector to Emitter Voltage	60 Volts	$ \langle \backslash \rangle \rangle$
BVebo Emitter to Base Voltage	4.0 Volts	$ / A \rangle$
Ic Collector Current	6.0 Amps Peak	
Maximum Temperatures		
Storage Temperature	- 65 to +150 °C	
Operating Junction Temperature	+ 200°C	

ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	ТҮР	MAX	UNITS
Pout Pin Pg η _c VSWR	Broadband Power Out Power Input Broadband Power Gain Collector Efficiency Load Mismatch Tolerance	F = 1025-1150 MHz Vcc = 50 Volts PW = 10 µsec DF =1% F = 1090 MHz	90 8.0 35	98 8.5 38	14 10:1	Watts Watts d B %

BVeboEmitter to Base BreakdownBVcesCollector to Emitter BreakdownCobCapacitance Collector to Baseh _{FE} DC - Current Gainθjc1Thermal Resistance	Ie = 1 mA Ie = 10 mA Vcb = 50 V Ic= 500mA,Vcc= 5V Tc= 25° C	3.5 65 15		16 120 0.6	Volts Volts pF °C/W	
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Note1: At Rated Power Output and pulse conditions.

2: Maximum Ratings are for RF Amplifier Operation

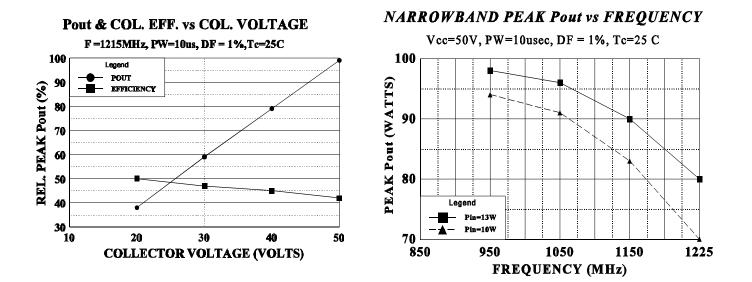
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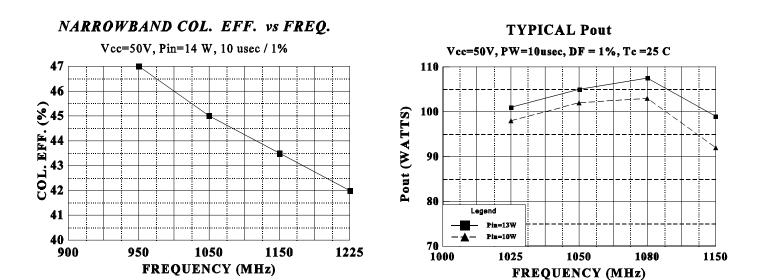
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GHz Technology Inc. 3000 Oakmead Village Drive, Santa Clara, CA 95051-0808 Tel. 408 / 986-8031 Fax 408 / 986-8120

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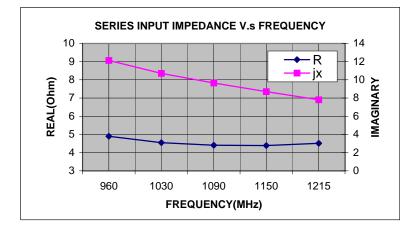
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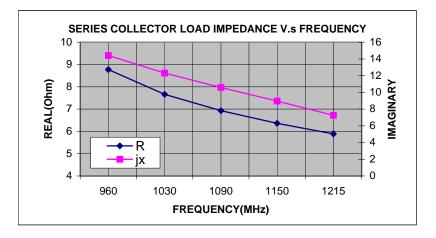
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VCB=50V Pout= 90Watts. PW 10uS, DF=1%

	Zin		ZCL	
Frequency	R	jx	R	jx
960	4.9	12.13	8.77	14.41
1030	4.55	10.71	7.66	12.3
1090	4.41	9.65	6.93	10.59
1150	4.39	8.7	6.36	8.95
1215	4.51	7.81	5.89	7.26





	F 2 A 4X 3
C Gold Plated	$\begin{array}{c} & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ \end{array}$ $\begin{array}{c} & & & \\ & & \\ & & \\ \end{array}$ $\begin{array}{c} & & \\ & & \\ & & \\ \end{array}$ $\begin{array}{c} & & \\ \end{array}$ $\begin{array}{c} & & \\ \end{array}$ $\begin{array}{c} & & \\ \end{array}$ $\begin{array}{c} & & \\ & \\ \end{array}$ $\begin{array}{c} & & \\ \end{array}$ \end{array} $\begin{array}{c} & & \\ \end{array}$ $\begin{array}{c} & & \\ \end{array}$ \end{array} \end{array} \end{array} $\begin{array}{c} & & \\ \end{array}$ \end{array} \end{array} \end{array} \end{array} \end{array} \end{array} \end{array} \end{array} \end{array}
DIM MILLIMETER TOL INCHES TOL A 5.71 .13 .225 .005 B 7.11 DIA .13 .280 DIA .005 C 0.13 .02 .005 .001 D 1.40 .13 .055 .005 E 25.53 .64 1.005 .025 F 45° 5° 45° 5° G 3.94 REF .155 REF	3 = EMITTER
CH2 TECHNOLOGY RF - MICROWAVE SILICON POWER TRANSISTORS	dwg no. 55FU